



SHEET 1 OF 1

INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.  
**060188-0766**SERIAL NO.  
**10/775,122**APPLICANT  
**Taiji NODA**FILING DATE  
**February 11, 2004**GROUP  
**2812**

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
CL		US 6,437,406 B1	8-20-2002	Lee	
CL		US 6,261,889 B1	7-17-2001	Ono	
CL		US 6,455,385 B1	9-24-2002	Alvis et al.	
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## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
CL		Der-Gao LIN et al., "The Effect of Fluorine on MOSFET Channel Length", 1 October 1993, IEEE Electron Device Letters, IEEE Service Center, New York, NY pp. 469-471, XP000397398

EXAMINER

*Chung Lin*

DATE CONSIDERED

5/1/06

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